

2020년 2월 14일(금), 09:00~10:30

Room B (에메랄드 II+III, 5층)

F. Silicon and Group-IV Devices and Integration Technology 분과
[FB1-F] Emerging Device Technology II

FB1-F-1 09:00~09:30	[초청] Static Negative Capacitance nFETs with 1nm Effective Oxide Thickness Gate Stack Daewoong Kwon <i>Electrical Engineering, Inha University</i>
FB1-F-2 09:30~09:45	Sensitivity Analysis of NCFET-based 6-T SRAM Yuri Hong and Changwan Shin <i>Department of Electrical and Computer Engineering, Sungkyunkwan University</i>
FB1-F-3 09:45~10:00	Precise Spectroscopic Analysis on Ultrathin Oxide Layer and Interfaces for Device Reliability Characterization Hyungtak Seo ^{1,2} , Hyunwoo Kang ² , and Shaid Iqbal ² ¹ <i>Department of Materials Science and Engineering, Ajou University,</i> ² <i>Department of Energy Systems Research, Ajou University</i>
FB1-F-4 10:00~10:15	Si Resonant Plasma-wave Transistor for Terahertz Detection Jong Yul Park, Min Woo Ryu, Sung-Ho Kim, and Kyung Rok Kim <i>School of Electrical and Computer Engineering, UNIST</i>
FB1-F-5 10:15~10:30	Impact of Bottom-Gate Biasing on Implant-free Junctionless Ge-on-Insulator n-MOSFETs Hyeong-Rak Lim ^{1,2,3} , Seong Kwang Kim ³ , Jae-Hoon Han ¹ , Hansung Kim ¹ , Dae-Myeong Geum ³ , Yun-Joong Lee ¹ , Young-Hun shin ¹ , Byeong-Kwon Ju ² , Hyung-Jun Kim ¹ , and Sanghyeon Kim ³ ¹ <i>KIST,</i> ² <i>School of Electrical Engineering, Korea University,</i> ³ <i>School of Electrical Engineering, KAIST</i>